



MMDT2227

SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

Complementary Pairs One 2222A Type (NPN) One 2907A Type (PNP)

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

Mechanical Data

Case: SOT-363

Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020C

Terminals: Solderable per MIL-STD-202, Method 208

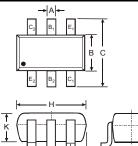
Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe)

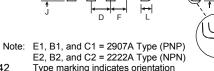
Terminal Connections: See Diagram

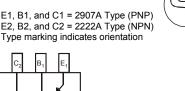
Ordering & Date Code Information: See Page 4

Marking Information: K27, See Page 4

Weight: 0.006 grams (approximate)







	SOT-363	
Dim	Min	Max
Α	0.10	0.30
В	1.15	1.35
С	2.00	2.20
D	0.65 N	ominal
F	0.30	0.40
Н	1.80	2.20
J	_	0.10
K	0.90	1.00
L	0.25	0.40
М	0.10	0.25
α	8	0
All Din	nensions	in mm

Maximum Ratings, Total Device @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, 2222A Type (NPN) @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous	I _C	600	mA

Maximum Ratings, 2907A Type (PNP) @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	Ic	-600	mA

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout
- document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

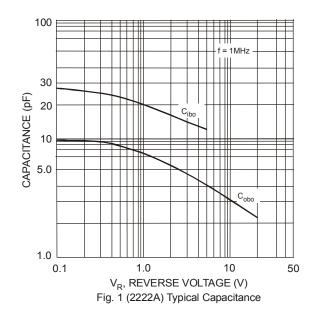
 Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

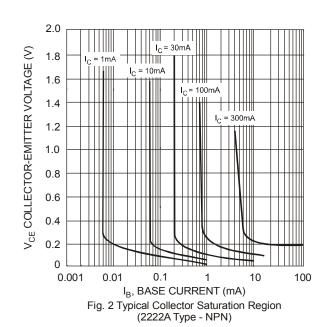


Electrical Characteristics, 2222A Type (NPN) @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)	- 7				
Collector-Base Breakdown Voltage	V _{(BR)CBO}	75	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	_	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	_	V	$I_E = 10\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}		10	nA μA	V _{CB} = 60V, I _E = 0 V _{CB} = 60V, I _E = 0, T _A = 150°C
Collector Cutoff Current	ICEX	_	10	nA	V _{CE} = 60V, V _{EB(OFF)} = 3.0V
Emitter Cutoff Current	I _{EBO}	_	10	nA	$V_{EB} = 3.0V, I_{C} = 0$
Base Cutoff Current	I _{BL}	_	20	nA	V _{CE} = 60V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h _{FE}	35 50 75 100 40 50 35	 300 	_	$\begin{array}{ll} I_{C} = 100 \mu A, \ V_{CE} = 10V \\ I_{C} = 1.0 mA, \ V_{CE} = 10V \\ I_{C} = 10 mA, \ V_{CE} = 10V \\ I_{C} = 150 mA, \ V_{CE} = 10V \\ I_{C} = 500 mA, \ V_{CE} = 10V \\ I_{C} = 10 mA, \ V_{CE} = 10V, \ T_{A} = -55^{\circ}C \\ I_{C} = 150 mA, \ V_{CE} = 1.0V \end{array}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.3 1.0	٧	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.6	1.2 2.0	٧	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}		8	pF	$V_{CB} = 10V, f = 1.0MHz, I_{E} = 0$
Input Capacitance	C _{ibo}		25	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$
Current Gain-Bandwidth Product	f⊤	300	_	MHz	$V_{CE} = 20V, I_{C} = 20mA,$ f = 100MHz
Noise Figure	NF		4.0	dB	V_{CE} = 10V, I_{C} = 100 μ A, R _S = 1.0k Ω , f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	10	ns	V _{CC} = 30V, I _C = 150mA,
Rise Time	t _r		25	ns	$V_{BE(off)} = -0.5V, I_{B1} = 15mA$
Storage Time	ts	_	225	ns	V _{CC} = 30V, I _C = 150mA,
Fall Time	t _f	_	60	ns	$I_{B1} = I_{B2} = 15\text{mA}$

Note: 5. Pulse test: Pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.



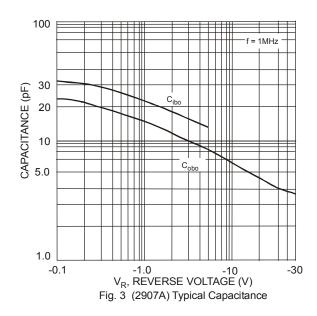


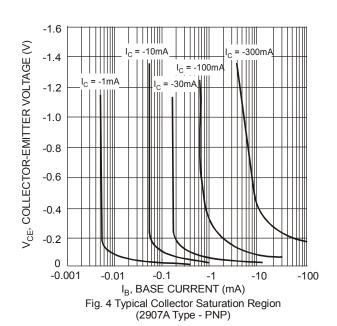


Electrical Characteristics, 2907A Type (PNP) @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)		•		•	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-60	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_	V	$I_{C} = -10 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	-10	nA μA	$V_{CB} = -50V$, $I_E = 0$ $V_{CB} = -50V$, $I_E = 0$, $T_A = 125$ °C
Collector Cutoff Current	I _{CEX}	_	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -0.5V
Base Cutoff Current	I _{BL}	_	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -0.5V
ON CHARACTERISTICS (Note 6)				•	
DC Current Gain	h _{FE}	75 100 100 100 50			$\begin{split} I_C &= -100 \mu A, \ V_{CE} = -10 V \\ I_C &= -1.0 m A, \ V_{CE} = -10 V \\ I_C &= -10 m A, \ V_{CE} = -10 V \\ I_C &= -150 m A, \ V_{CE} = -10 V \\ I_C &= -500 m A, \ V_{CE} = -10 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-0.4 -1.6	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	-1.3 -2.6	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS		•		•	
Output Capacitance	C _{obo}	_	8.0	pF	$V_{CB} = -10V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{ibo}	_	30	pF	V _{EB} = -2.0V, f = 1.0MHz, I _C = 0
Current Gain-Bandwidth Product	f⊤	200	_	MHz	V _{CE} = -20V, I _C = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}		45	ns	_
Delay Time	t _d	_	10	ns	V _{CC} = -30V, I _C = -150mA,
Rise Time	t _r	_	40	ns	I _{B1} = -15mA
Turn-Off Time	t _{off}	_	100	ns	
Storage Time	t _s	_	80	ns	V _{CC} = -6.0V, I _C = -150mA,
Fall Time	t _f	_	30	ns	$I_{B1} = I_{B2} = -15\text{mA}$

Notes: 6. Short duration pulse test used to minimize self-heating effect.





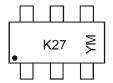


Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT2227-7-F	SOT-363	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K27 = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	Г	М	Ν	Р	R	S	Т	U	V	W	X	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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